

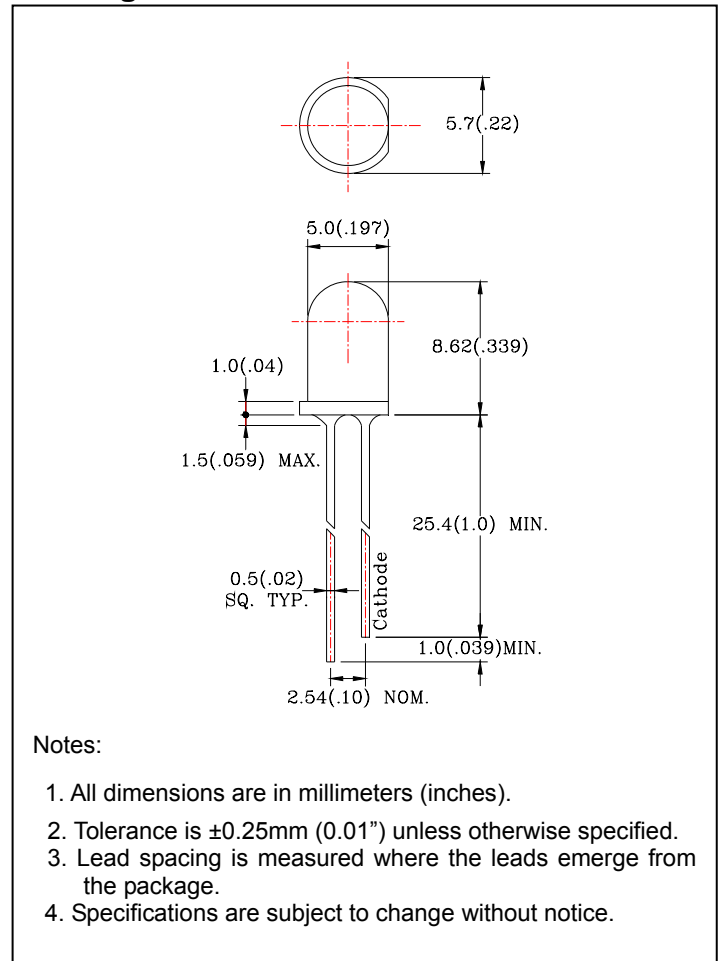
● **Features:**

1. Chip material: GaAsP/GaP
2. Emitted color : Hi-Eff Red
3. Lens Appearance : Red Diffused
4. Low power consumption.
5. High efficiency.
6. Versatile mounting on P.C. Board or panel.
7. Low current requirement.
8. T-1 3/4 type package
9. This product don't contained restriction substance, compliance ROHS standard.

● **Applications:**

1. TV set
2. Monitor
3. Telephone
4. Computer
5. Circuit board

● **Package dimensions:**



● **Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Power Dissipation	Pd	14	mW
Forward Current	I _F	7	mA
Reverse Voltage	V _R	5	V
Operating Temperature	Topr	-40°C~80°C	
Storage Temperature	Tstg	-40°C~85°C	
Soldering Temperature	Tsol	260°C (for 5 seconds)	

*1 Condition for I_{FP} is pulse of 1/10 duty and 0.1msec width.

● Electrical and optical characteristics(Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	I _F =2mA	-	1.8	2.2	V
Luminous Intensity	Iv	I _F =2mA	-	6.5	-	mcd
Reverse Current	IR	V _R =5V	-	-	100	μA
Peak Wave Length	λ _p	I _F =20mA	-	640	-	nm
Dominant Wave Length	λ _d	I _F =20mA	617	-	638	nm
Spectral Line Half-width	Δλ	I _F =20mA	-	40	-	nm
Viewing Angle	2θ1/2	I _F =20mA	-	40	-	deg

● Typical Electro-Optical Characteristics Curves

Fig.1 Relative intensity vs. Wavelength

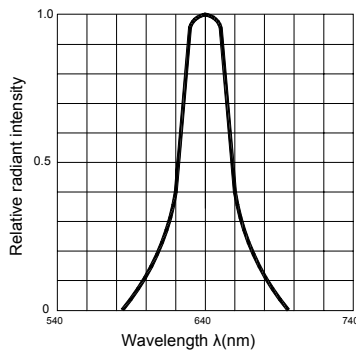


Fig.2 Forward current derating curve vs. Ambient temperature

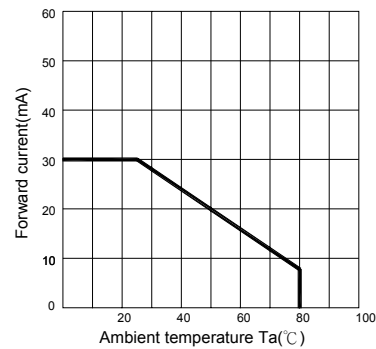


Fig.3 Forward current vs. Forward voltage

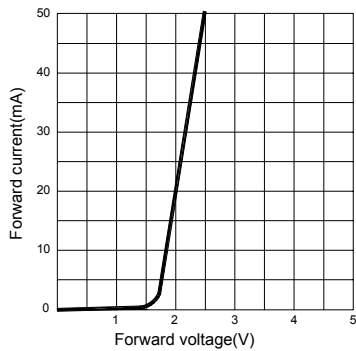


Fig.4 Relative luminous intensity vs. Ambient temperature

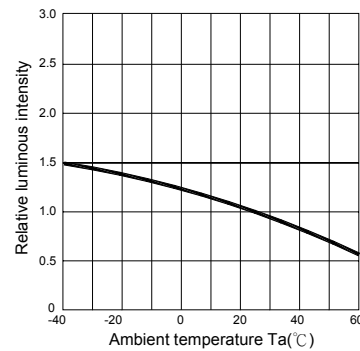


Fig.5 Relative luminous intensity vs. Forward current

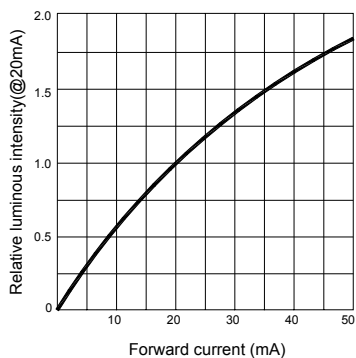


Fig.6 Radiation diagram

